

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: kiyoshi IRINO

Serial No.: Divisional of SN 08/917,936

Art Unit: Not Yet Assigned

Filed: Herewith

Examiner: Not Yet Assigned

For: METHOD OF FABRICATING A SEMICONDUCTOR
DEVICE CONTAINING NITROGEN IN A GATE OXIDE
FILM (As Amended)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

October 27, 1999

Sir:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE TITLE:

Please amend the title to read:

--METHOD OF FABRICATING A SEMICONDUCTOR DEVICE
CONTAINING NITROGEN IN A GATE OXIDE FILM--.

IN THE CLAIMS:

Please cancel claims 1-5 and 14.

REMARKS

Claims 6-13 are pending. The above amendments are believed to place the application in better condition for examination.

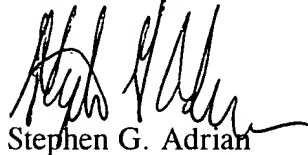
Prompt and favorable action on the merits is earnestly solicited.

0942805-10229
662207-25082460

In the event any fees are required in connection with this paper, please charge Deposit
Account No. 01-2340.

Respectfully submitted,

ARMSTRONG, WESTERMAN, HATTORI,
McLELAND & NAUGHTON



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